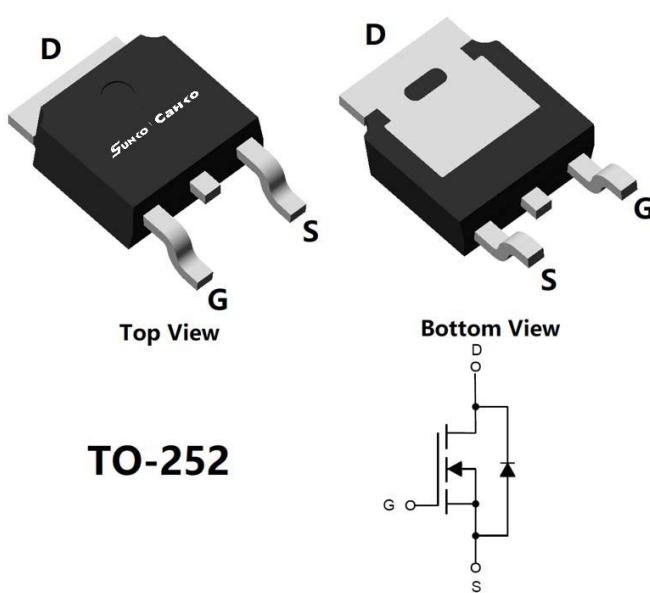


P-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} -100V
- I_D -28A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) <58 mohm
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) <65 mohm
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Load Switch
- Battery Protection

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_c=25^\circ\text{C}$	I_D	-28	A
	$T_c=100^\circ\text{C}$		-17.8	
Pulsed Drain Current ^A		I_{DM}	-112	A
Avalanche energy ^B		E_{AS}	220	mJ
Total Power Dissipation	$T_c=25^\circ\text{C}$	P_D	96	W
	$T_c=100^\circ\text{C}$		38	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	°C

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D		$R_{\theta JA}$	16	20	°C/W
Thermal Resistance Junction-to-Ambient ^D	Steady-State		45	55	
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1	1.3	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCD28GP10A	F1/F2	SCD28GP10A	2500	2500	25000	13" reel

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions		Min	Typ	Max	Units
Static Parameter							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$		-100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-100\text{V}, V_{\text{GS}}=0\text{V}$	$T_J=25^\circ\text{C}$			-1	μA
			$T_J=55^\circ\text{C}$			-5	
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}= \pm 20\text{V}, V_{\text{DS}}=0\text{V}$				± 100	nA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$		-1.0	-1.8	-2.5	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}= -10\text{V}, I_{\text{D}}=-15\text{A}$			42	58	$\text{m}\Omega$
		$V_{\text{GS}}= -4.5\text{V}, I_{\text{D}}=-7\text{A}$			46	65	
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=-20\text{A}, V_{\text{GS}}=0\text{V}$				-1.3	V
Maximum Body-Diode Continuous Current	I_{S}					-28	A
Dynamic Parameters							
Input Capacitance	C_{iss}	$V_{\text{DS}}=-50\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$			2100		pF
Output Capacitance	C_{oss}				236		
Reverse Transfer Capacitance	C_{rss}				48		
Switching Parameters							
Total Gate Charge	$Q_g(-10\text{V})$	$V_{\text{GS}}=-10\text{V}, V_{\text{DS}}=-50\text{V}, I_{\text{D}}=-5\text{A}$			40		nC
Total Gate Charge	$Q_g(-4.5\text{V})$				19.4		
Gate-Source Charge	Q_{gs}				7.8		
Gate-Drain Charge	Q_{gd}				8.6		
Reverse Recovery Charge	Q_{rr}	$I_{\text{F}}=-5\text{A}, di/dt=100\text{A/us}$			280		ns
Reverse Recovery Time	t_{rr}				104		
Turn-on Delay Time	$t_{\text{D(on)}}$				13		
Turn-on Rise Time	t_{r}				39		
Turn-off Delay Time	$t_{\text{D(off)}}$	$V_{\text{GS}}=-10\text{V}, V_{\text{DD}}=-50\text{V}, I_{\text{DS}}=-5\text{A}$ $R_{\text{GEN}}=6\Omega$			100.1		
Turn-off fall Time	t_{f}				105.3		

- A. Repetitive rating; pulse width limited by max. junction temperature.
B. $V_{\text{DD}}=50\text{V}, R_{\text{G}}=25\Omega, L=1\text{mH}, I_{\text{AS}}=31\text{A}$.
C. P_d is based on max. junction temperature, using junction-case thermal resistance.
D. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $TA = 25^\circ\text{C}$. The Power dissipation PDSM is based on $R_{\theta JA} \leq 10\text{s}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design

■ Typical Performance Characteristics

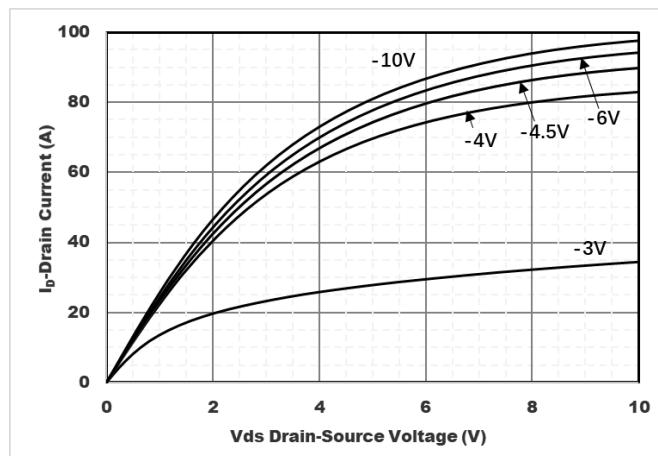


Figure1. Output Characteristics

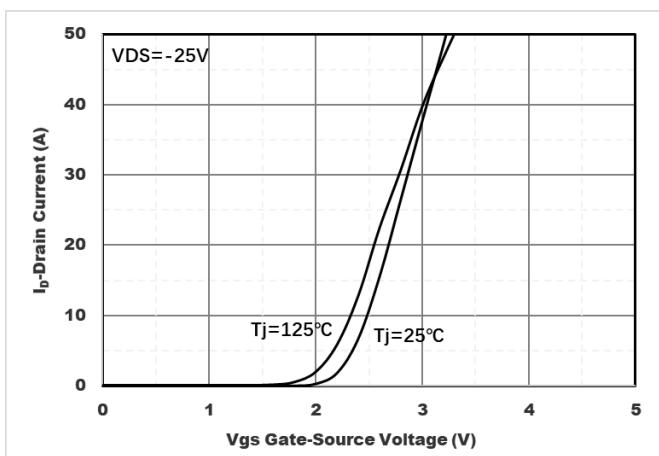


Figure2. Transfer Characteristics

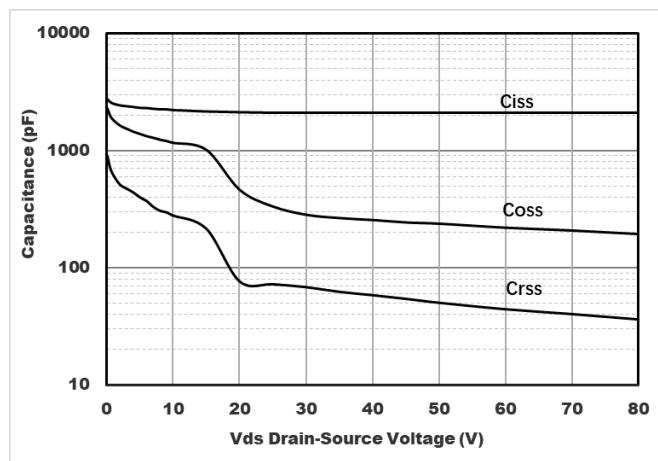


Figure3. Capacitance Characteristics

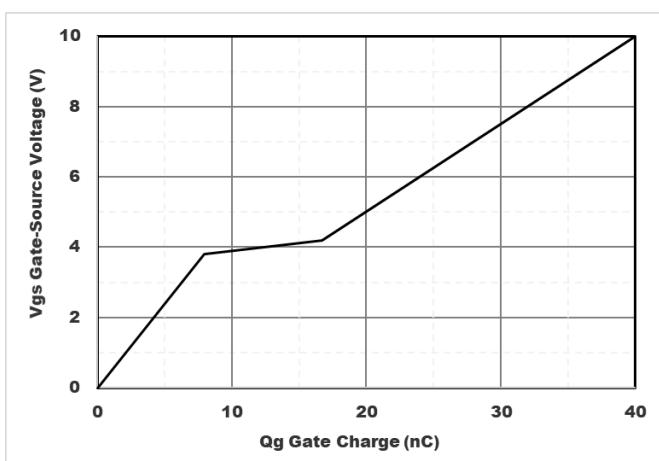


Figure4. Gate Charge

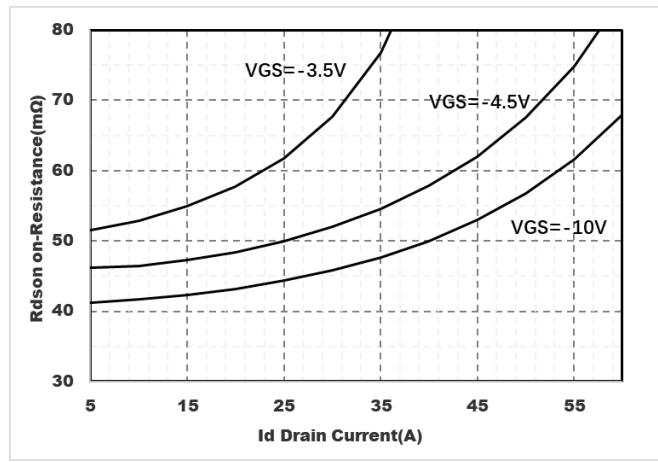


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

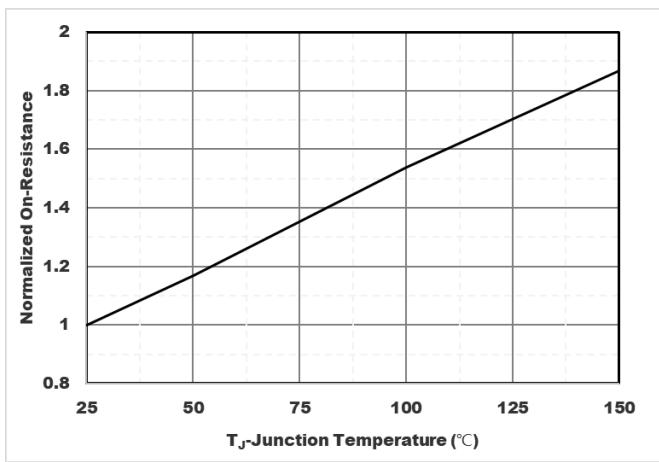


Figure6. Normalized On-Resistance

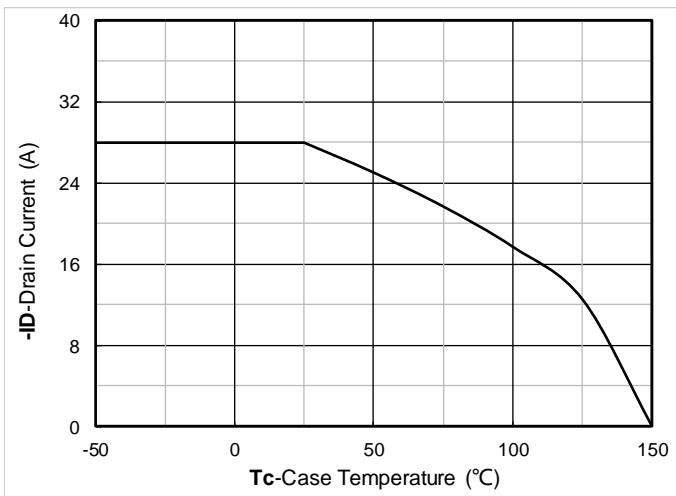


Figure 7. Drain current

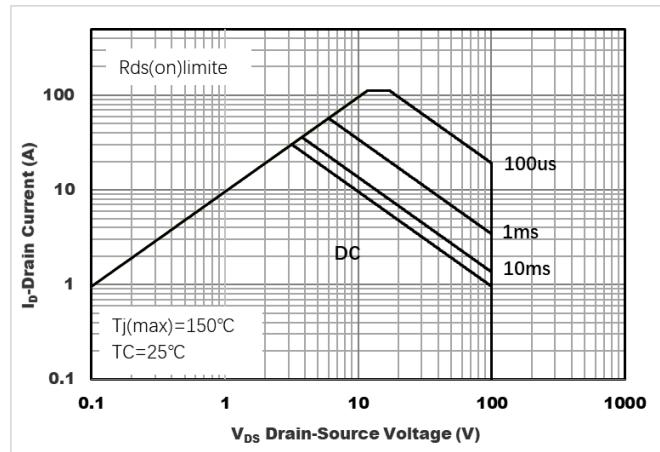


Figure 8. Safe Operation Area

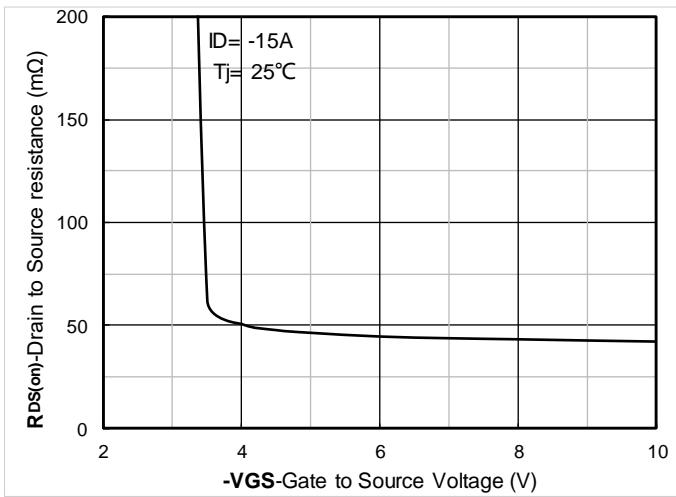


Figure 9. On-Resistance vs Gate to Source Voltage

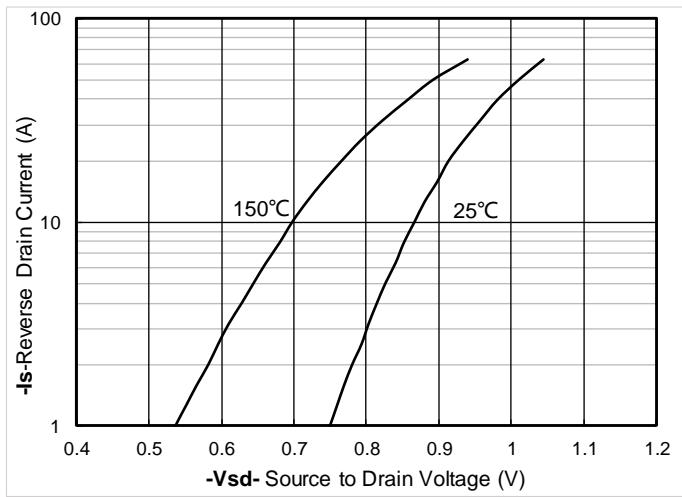


Figure 10. Forward characteristics of reverse diode

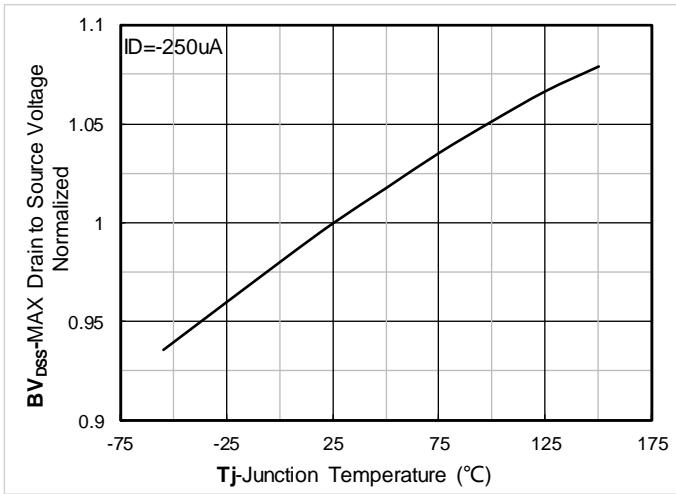


Figure 11. Normalized breakdown voltage

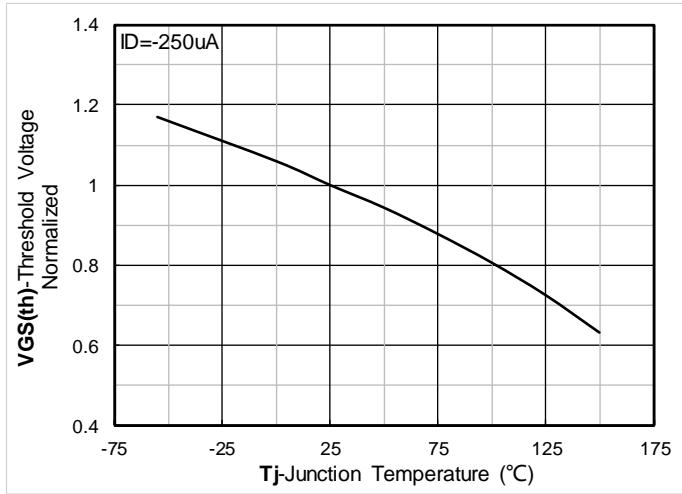


Figure 12. Normalized Threshold voltage

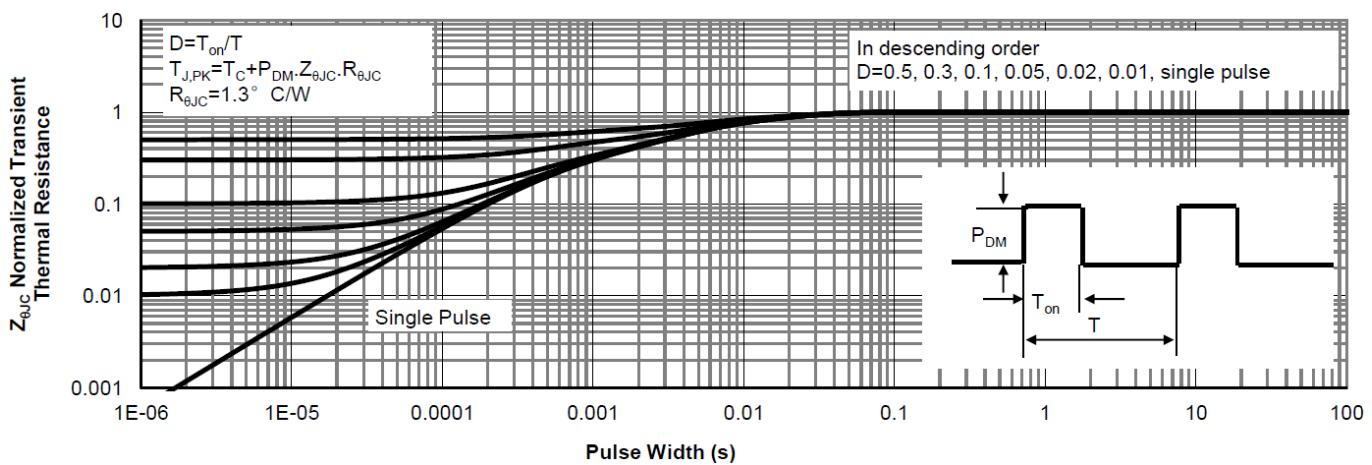
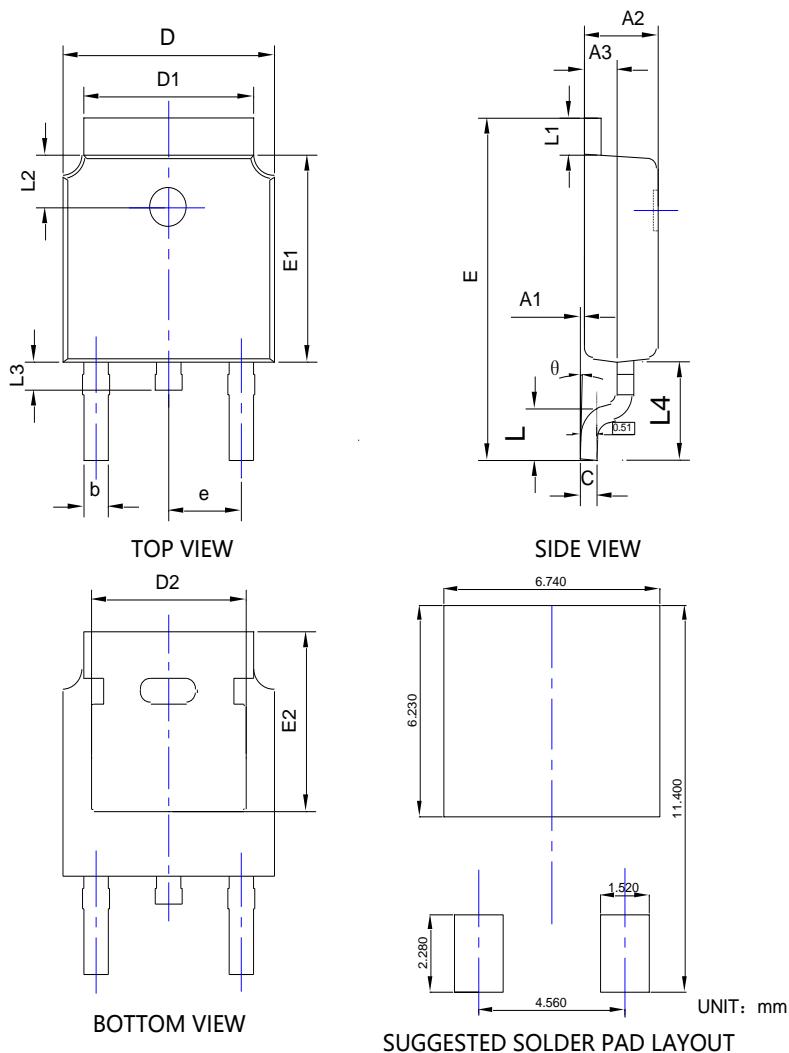


Figure13.Normalized Maximum Transient thermal impedance

■ TO-252-B Package Information



SYMBOL	DIMENSIONS			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.008	0.000	---	0.200
A2	0.087	0.091	0.094	2.200	2.300	2.400
A3	0.035	0.039	0.043	0.900	1.000	1.100
b	0.026	0.030	0.034	0.660	0.760	0.860
c	0.018	0.020	0.023	0.460	0.520	0.580
D	0.256	0.260	0.264	6.500	6.600	6.700
D1	0.203	0.209	0.215	5.150	5.300	5.450
D2	0.181	0.189	0.195	4.600	4.800	4.950
E	0.390	0.398	0.406	9.900	10.100	10.300
E1	0.236	0.240	0.244	6.000	6.100	6.200
E2	0.203	0.209	0.215	5.150	5.300	5.450
e	0.090BSC			2.286BSC		
L	0.049	0.059	0.069	1.250	1.500	1.750
L1	0.035	---	0.050	0.900	---	1.270
L2	0.055	---	0.075	1.400	---	1.900
L3	0.024	0.031	0.039	0.600	0.800	1.000
L4	0.114REF			2.900REF		
theta	0°	---	10°	0°	---	10°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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